DMC90401

Silicon NPN epitaxial planar type

For general amplification

DMC50401 in SSMini6 type package

Features

- \bullet High forward current transfer ratio h_{FE} with excellent linearity
- \bullet Low collector-emitter saturation voltage $V_{CE(\text{sat})}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

Basic Part Number

Double DSC2001 (Individual)

Packaging

DMC904010R Embossed type (Thermo-compression sealing): 8000 pcs / reel (standard)

Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	60	V	
Collector-emitter voltage (Base open)	V _{CEO}	50	V	
Emitter-base voltage (Collector open)	V _{EBO}	7	V	
Collector current	I _C	100	mA	
Peak collector current	I _{CP}	200	mA	
Total power dissipation	P _T	125	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Package

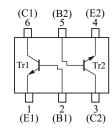
Code
 SSMini6-F3-B
 Package dimension clicks here.→

Pin Name

- 1: Emitter (Tr1)
 4: Emitter (Tr2)

 2: Base (Tr1)
 5: Base (Tr2)
- 3: Collector (Tr2) 6: Collector (Tr1)
- Marking Symbol: A8

Internal Connection



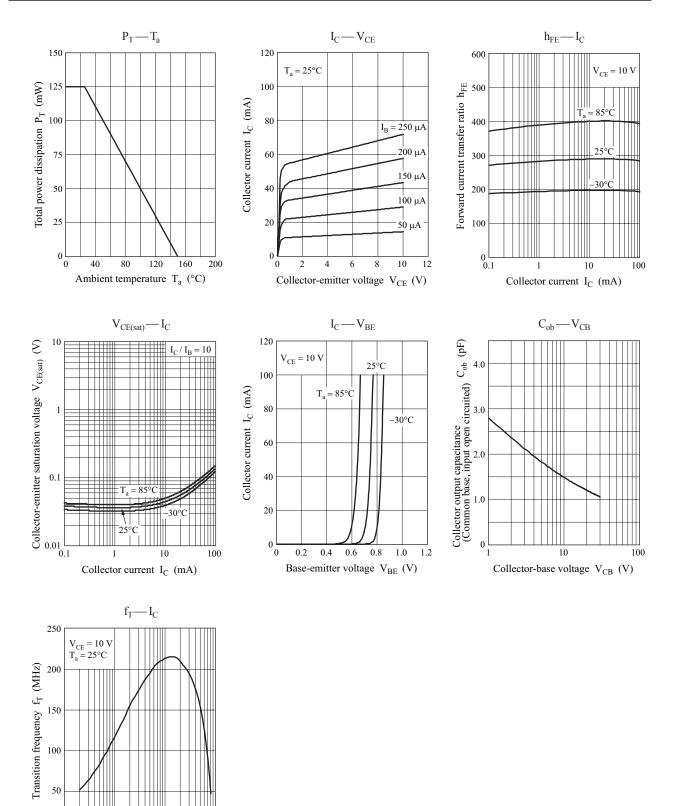
Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	60			V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = 2 {\rm mA}, I_{\rm B} = 0$	50			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	7			V
Collector-base cutoff current (Emitter open)	I _{CBO}	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			100	μΑ
Forward current transfer ratio	\mathbf{h}_{FE}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	210		460	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	f_{T}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		1.5		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

DMC90401

Panasonic



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Collector current I_C (mA)

1

100

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